

MCC

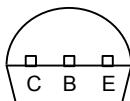
Micro Commercial Components
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MPSA55
MPSA56

Features

- Capable of 1.5Watts of Power Dissipation.
- Collector-current 500mA
- Collector-base Voltage 80V
- Operating and storage junction temperature range: -55°C to +150°C

Pin Configuration
Bottom View



Maximum Ratings

Symbol	Rating	Rating	Unit
V_{CEO}	Collector-Emitter Voltage	80	V
V_{CBO}	Collector-Base Voltage	80	V
V_{EBO}	Emitter-Base Voltage	4.0	V
I_C	Collector Current Continuous	500	mA
P_D	Total Device Dissipation @ $T_A=25^\circ\text{C}$ Derate above 25°C	625 5.0	mW mW/ $^\circ\text{C}$
P_D	Total Device Dissipation @ $T_A=25^\circ\text{C}$ Derate above 25°C	1.5 12	W mW/ $^\circ\text{C}$
T_J	Junction Temperature	-55 to +150	$^\circ\text{C}$
T_{STG}	Storage Temperature	-55 to +150	$^\circ\text{C}$

Electrical Characteristics @ 25°C Unless Otherwise Specified

Symbol	Parameter	Min	Max	Units
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OFF CHARACTERISTICS

$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage ⁽¹⁾ ($b=1.0\text{mAdc}$, $b=0$)	MPSA55 MPSA56	60 80	Vdc
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage ($b=100\text{uAdc}$, $b=0$)		4.0	Vdc
I_{CES}	Collector Cutoff Current ($V_{CE}=60\text{Vdc}$, $b=0$)		0.1	uAdc
I_{BO}	Collector Cutoff Current ($V_{CB}=60\text{Vdc}$, $b=0$) ($V_{CB}=80\text{Vdc}$, $b=0$)	MPSA55 MPSA56	0.1 0.1	uAdc

ON CHARACTERISTICS⁽¹⁾

$h_{FE(1)}$	DC Current Gain ($b=10\text{mAdc}$, $V_{CE}=1.0\text{Vdc}$)	100		
$h_{FE(2)}$	DC Current Gain ($b=100\text{mAdc}$, $V_{CE}=1.0\text{Vdc}$)	100		
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage ($b=100\text{mAdc}$, $b=10\text{mAdc}$)		0.25	Vdc
$V_{BE(on)}$	Base-Emitter Saturation Voltage ($b=100\text{mAdc}$, $V_{CE}=1.0\text{Vdc}$)		1.2	Vdc

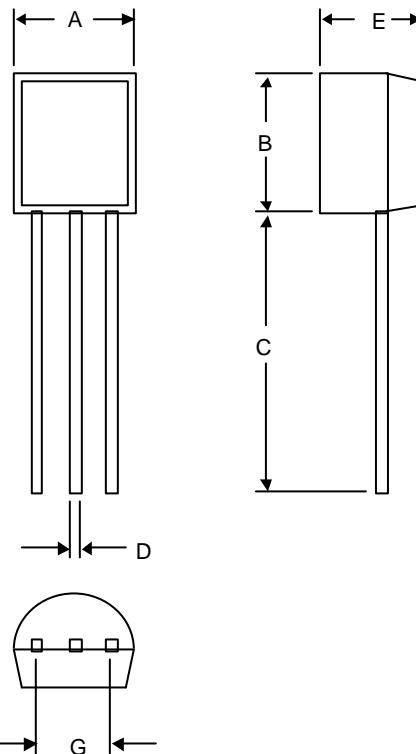
SMALL-SIGNAL CHARACTERISTICS

f_T	Current-Gain – Bandwidth Product ⁽³⁾ ($b=100\text{mAdc}$, $V_{CE}=1.0\text{Vdc}$, $f=100\text{MHz}$)	MPSA55 MPSA56	50	MHz
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1. Pulse Test: Pulse Width<300us, Duty Cycle<2.0%
2. f_T is defined as the frequency at which $|h_{fe}|$ extrapolates to unity.

PNP Silicon Amplifier Transistor

TO-92



DIM	DIMENSIONS				NOTE
	INCHES		MM		
	MIN	MAX	MIN	MAX	
A	.175	.185	4.45	4.70	
B	.175	.185	4.46	4.70	
C	.500	---	12.7	---	
D	.016	.020	0.41	0.63	
E	.135	.145	3.43	3.68	
G	.095	.105	2.42	2.67	